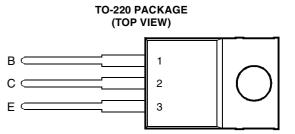
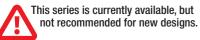
BDW24, BDW24A, BDW24B, BDW24C PNP SILICON POWER DARLINGTONS

BOURNS®

- Designed for Complementary Use with BDW23, BDW23A, BDW23B and BDW23C
- 50 W at 25°C Case Temperature
- 6 A Continuous Collector Current
- Minimum h_{FE} of 750 at 2 A, 3 V





Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT		
	BDW24		-45		
Collector-base voltage (I _E = 0)	BDW24A	V	-60	v	
	BDW24B	V _{CBO}	-80	v	
	BDW24C		-100		
	BDW24		-45		
Collector omitter voltage (I 0)	BDW24A	V	-60	V	
Collector-emitter voltage ($I_B = 0$)	BDW24B	V _{CEO}	-80	v	
	BDW24C		-100		
Emitter-base voltage	V _{EBO}	-5	V		
Continuous collector current		Ι _C	-6	А	
Continuous base current	I _B	-0.2	А		
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	P _{tot}	50	W		
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P _{tot}	2	W		
Operating junction temperature range	Тj	-65 to +150	°C		
Storage temperature range	T _{stg}	-65 to +150	°C		
Operating free-air temperature range	T _A	-65 to +150	°C		

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.4 W/°C.

2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

BDW24, BDW24A, BDW24B, BDW24C PNP SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS				MIN	ТҮР	MAX	UNIT
N	Collector-emitter	100 mA		(and Note 2)	BDW24 BDW24A	-45 -60			V
V _{(BR)CEO}	breakdown voltage	l _C = -100 mA	I _B = 0	(see Note 3)	BDW24B BDW24C	-80 -100			v
		V _{CE} = -30 V	I _B = 0		BDW240	-100		-0.5	
I _{CEO}	Collector-emitter	$V_{CE} = -30 V$	$I_{B} = 0$		BDW24A			-0.5	mA
	cut-off current	$V_{CE} = -40 V$	-		BDW24B			-0.5	
		V _{CE} = -50 V	-		BDW24C			-0.5	
	Collector cut-off current	$V_{CB} = -45 V$			BDW24			-0.2	
1		V _{CB} = -60 V	$I_E = 0$		BDW24A			-0.2	mA
I _{СВО}		V _{CB} = -80 V	$I_E = 0$		BDW24B			-0.2	ША
		V _{CB} = -100 V	$I_E = 0$		BDW24C			-0.2	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	$I_{\rm C} = 0$					-2	mA
	Forward current transfer ratio	V _{CE} = -3 V	-			1000			
h _{FE}		V _{CE} = -3 V		(see Notes 3 and 4)	14)	750		20000	
		V _{CE} = -3 V				100			
V _{CE(sat)}		I _B = -8 mA	-	(see Notes 3 and 4)			-2	V	
OE(Sat)	saturation voltage	I _B = -60 mA	I _C = -6 A		•			-3	
V _{BE(sat)}	Base-emitter saturation voltage	D	I _C = -2 A	(see Notes 3 and	l 4)			-2.5	V
V _{BE(on)}	Base-emitter	V _{CE} = -3 V		(see Notes 3 and 4)	(4)			-2.5	V
- BE(OU)	voltage	V _{CE} = -3 V	I _C = -6 A		,			-3	<u> </u>
V_{EC}	Parallel diode forward voltage	I _E = -2 A	$I_B = 0$					-1.8	V

NOTES: 3. These parameters must be measured using pulse techniques, t_p = 300 µs, duty cycle \leq 2%.

4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R _{θJC}	Junction to case thermal resistance			2.5	°C/W
R _{θJA}	Junction to free air thermal resistance			62.5	°C/W

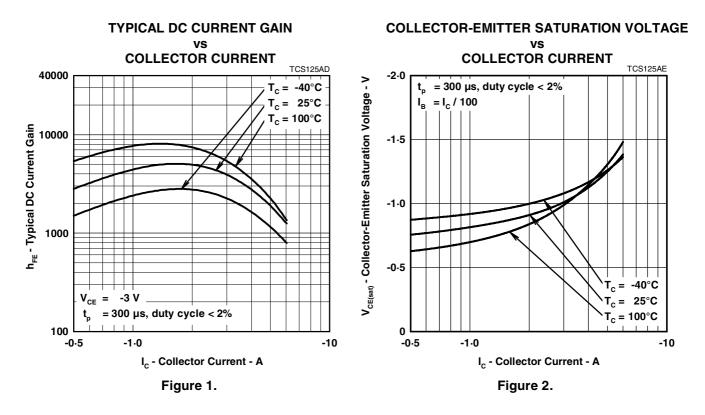
resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on}	Turn-on time	I _C = -3 A	I _{B(on)} = -12 mA	$I_{B(off)} = 12 \text{ mA}$		1		μs
t _{off}	Turn-off time	$V_{BE(off)} = 4.5 V$	$R_L = 10 \ \Omega$	t_p = 20 μ s, dc \leq 2%		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS

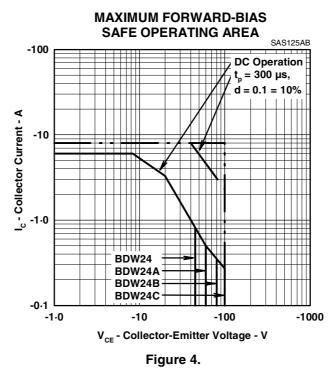


BASE-EMITTER SATURATION VOLTAGE vs **COLLECTOR CURRENT** TCS125AF -3.0 -40°C = V_{BE(sat)} - Base-Emitter Saturation Voltage - V тс 25°C Tc = 100°C -2.0 -2.5 -1.0 -1.5 = I_c / 100 I_B = 300 μ s, duty cycle < 2% -0.5 -0.5 -1.0 -10 I_c - Collector Current - A Figure 3.



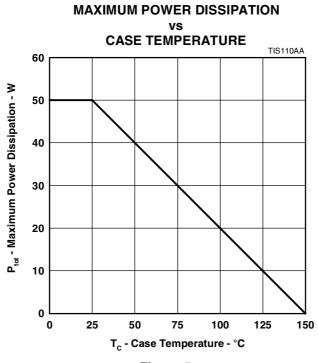
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MAXIMUM SAFE OPERATING REGIONS











PRODUCT INFORMATION

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